

Figure 1: Grazing incidence XRD pattern (top) from a WS_2 thin film deposited by low pressure CVD using $[(WSCl_4)_2(iPrS(CH_2)_2S^iPr)]$ at $700^\circ C$. The broad feature at $2\theta = 20-25^\circ$ is from the SiO_2 substrate, XRD pattern for bulk WS_2 (bottom). Run 1.

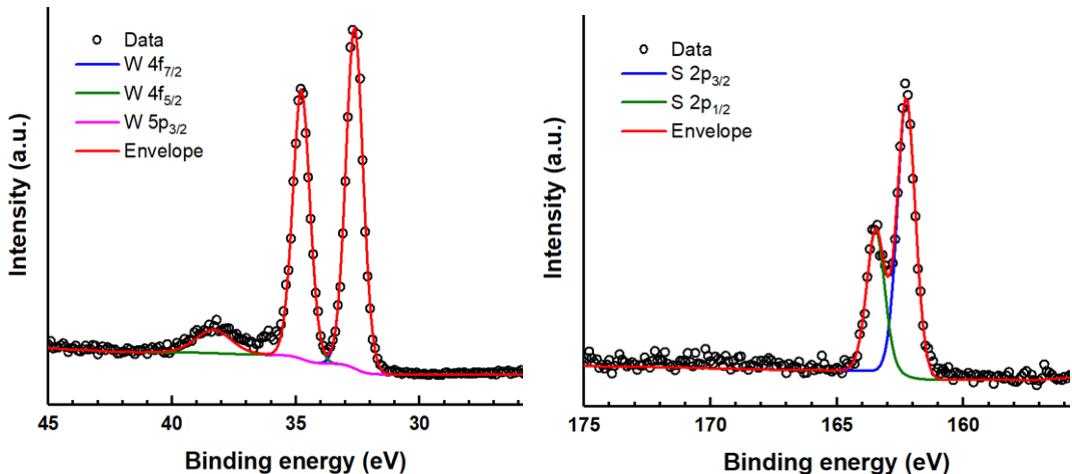


Figure 2: Representative XPS data for an as-deposited WS_2 film thin film via low pressure CVD using $[(WSCl_4)_2(iPrS(CH_2)_2S^iPr)]$. Showing the peaks associated with tungsten (left) and sulfur (right). Run 1.

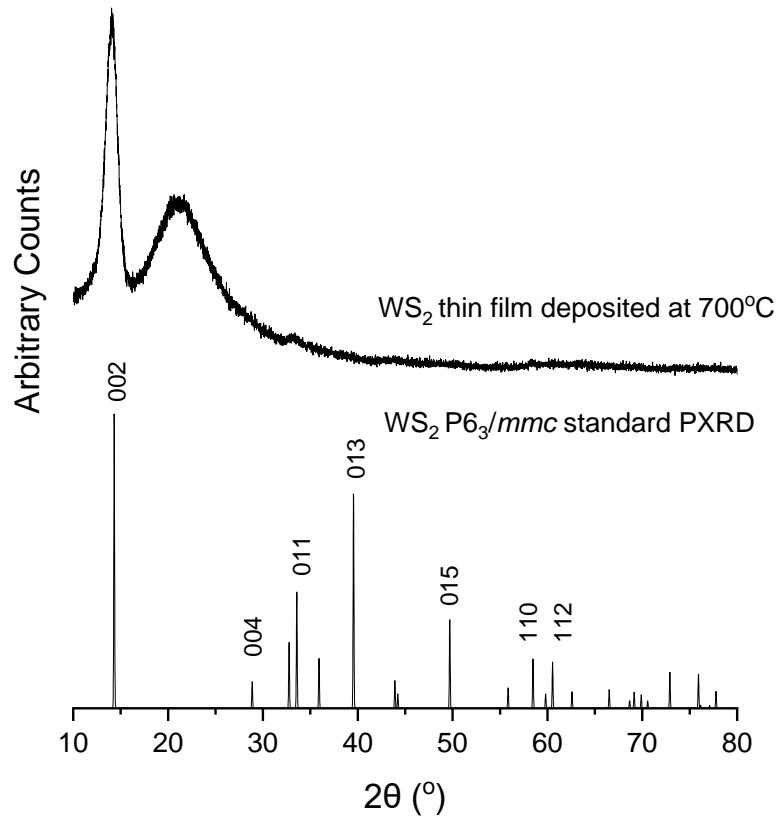


Figure 3: Grazing incidence XRD pattern (top) from a WS_2 thin film deposited by low pressure CVD using $[(WSCl_4)_2(iPrS(CH_2)_2S^iPr)]$ at $700^\circ C$. The broad feature at $2\theta = 20 - 25^\circ$ is from the SiO_2 substrate, XRD pattern for bulk WS_2 (bottom). Run 2.

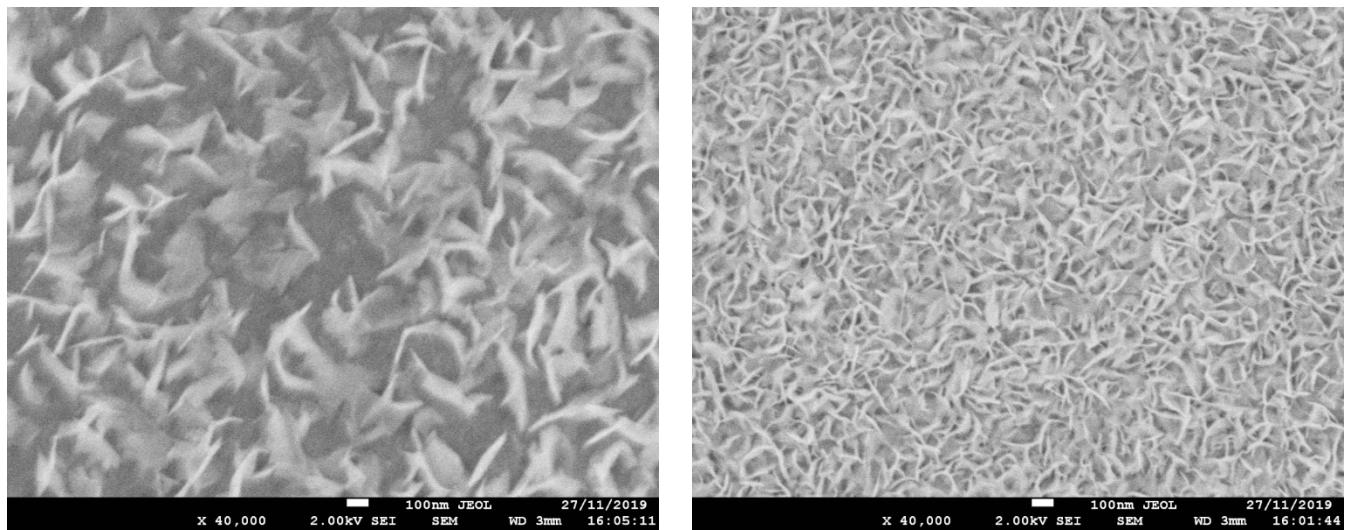


Figure 4: SEM image showing a continuous WS_2 thin film produced via low pressure CVD using $[(WSCl_4)_2(iPrS(CH_2)_2S^iPr)]$ at $700^\circ C$. Run 2.

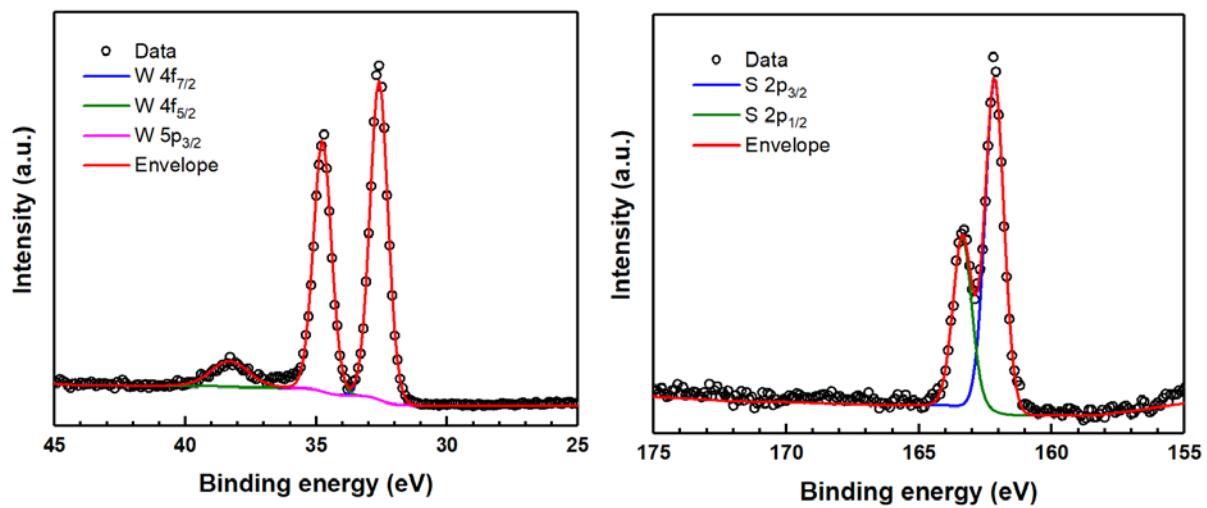


Figure 5: Representative XPS data for an as-deposited WS_2 film thin film via low pressure CVD using $[(WSCI_4)_2(iPrS(CH_2)_2S'iPr)]$. Showing the peaks associated with tungsten (left) and sulfur (right). Run 2.

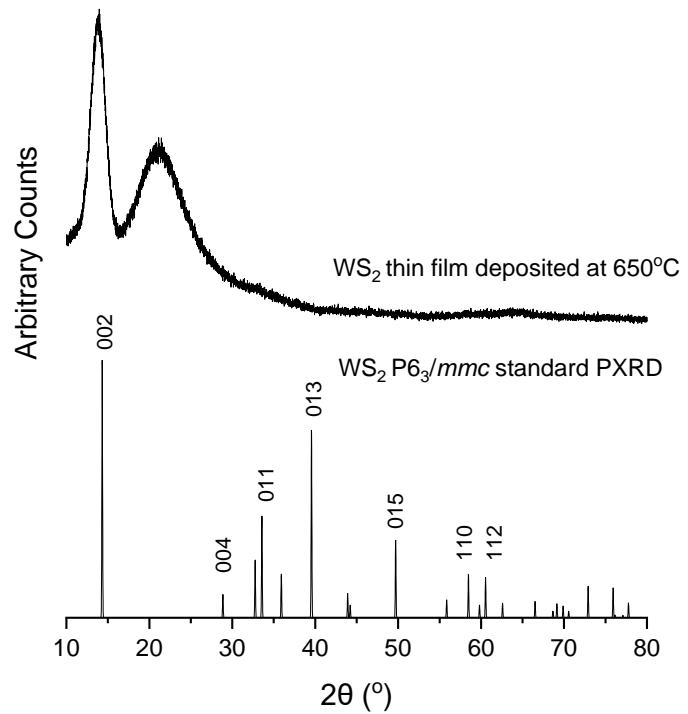


Figure 6: Grazing incidence XRD pattern (top) from a WS_2 thin film deposited by low pressure CVD using $[(WSCI_4)_2(iPrS(CH_2)_2S'iPr)]$ at $650^\circ C$. The broad feature at $2\theta = 20 - 25^\circ$ is from the SiO_2 substrate, XRD pattern for bulk WS_2 (bottom). Run 3.

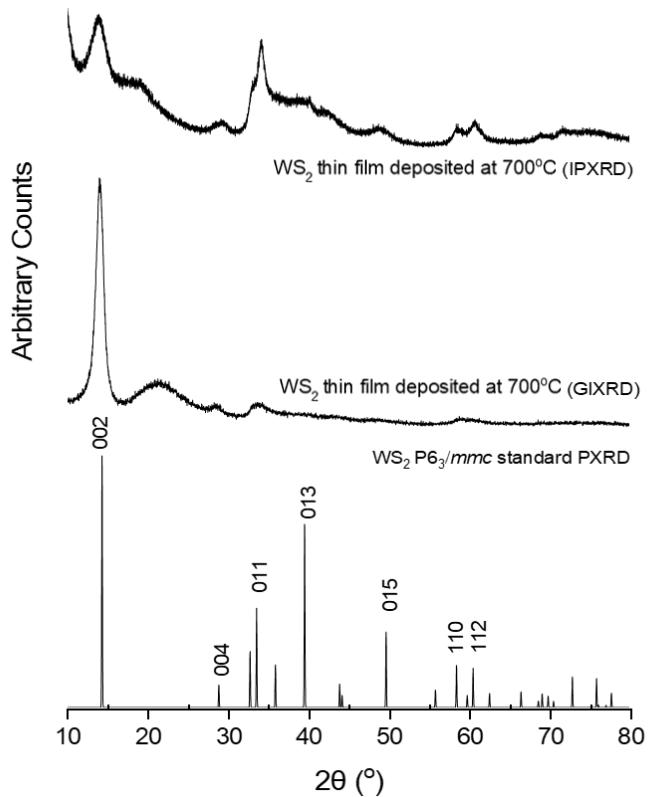


Figure.7: In-plane XRD pattern (top), grazing incidence XRD pattern (middle) from a WS₂ thin film deposited by low pressure CVD using [WSCl₄(SⁿBu₂)] at 700 °C. The broad feature at $2\theta = 20 - 25^\circ$ is from the SiO₂ substrate, XRD pattern for bulk WS₂ (bottom). Run 4.

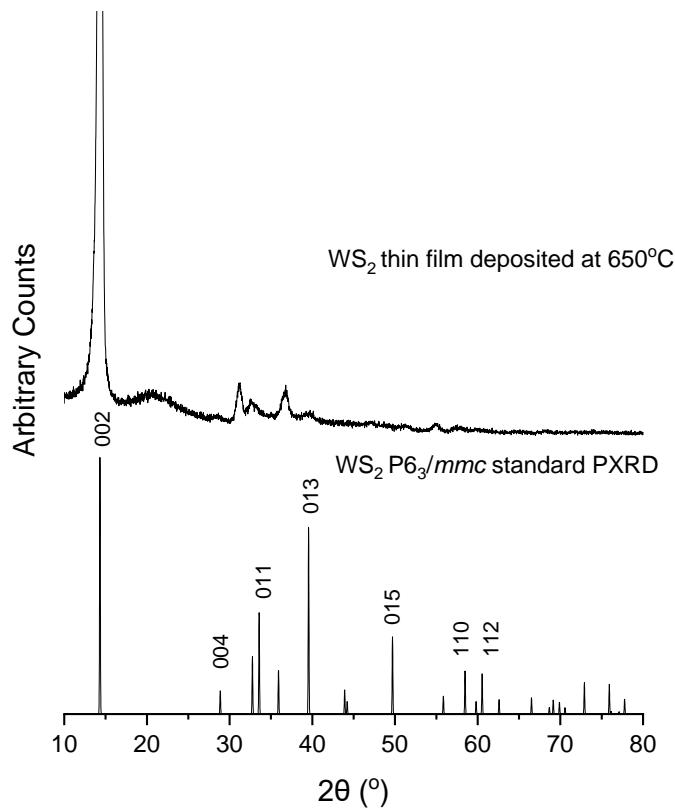


Figure.8: Grazing incidence XRD pattern (top) from a WS₂ thin film deposited by low pressure CVD using [WSCl₄(SⁿBu₂)] at 650 °C. The broad feature at $2\theta = 20 - 25^\circ$ is from the SiO₂ substrate, XRD pattern for bulk WS₂ (bottom). Run 5.

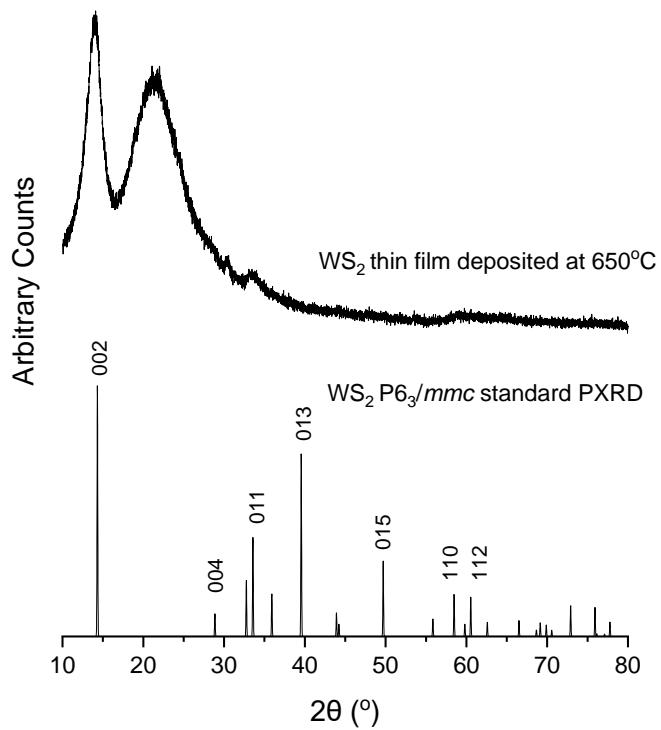


Figure.9: Grazing incidence XRD pattern (top) from a WS₂ thin film deposited by low pressure CVD using [WSCl₄(SⁿBu₂)] at 650 °C. The broad feature at $2\theta = 20 - 25^\circ$ is from the SiO₂ substrate, XRD pattern for bulk WS₂ (bottom). Run 6.

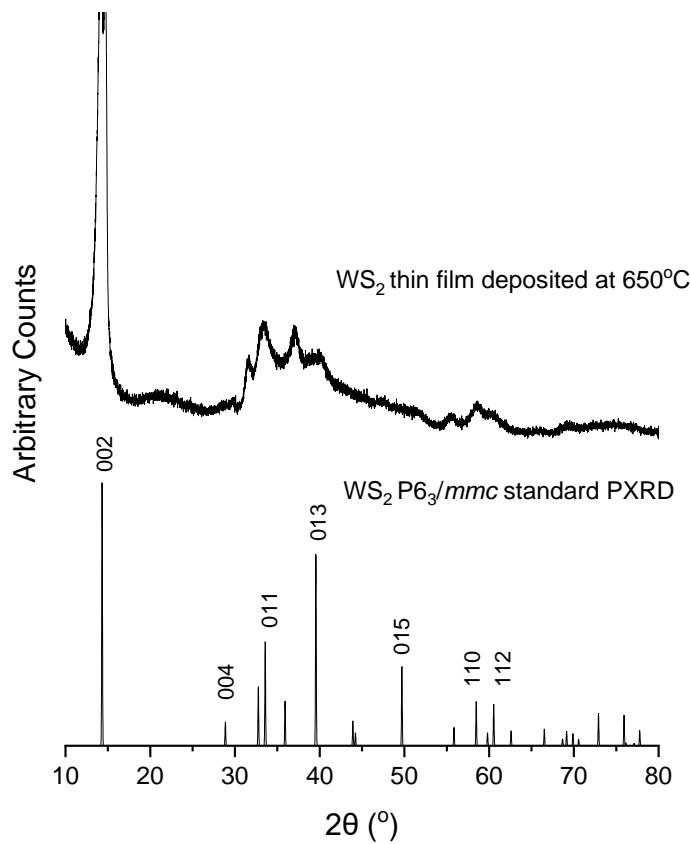


Figure.10: Grazing incidence XRD pattern (top) from a WS₂ thin film deposited by low pressure CVD using [WSCl₄(SⁿBu₂)] at 650 °C. The broad feature at $2\theta = 20 - 25^\circ$ is from the SiO₂ substrate, XRD pattern for bulk WS₂ (bottom). Run 7.